EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	68479	semiconductor adj wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/22 08:56
S2	7489	cleaning and (semiconductor adj wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/21 09:30
S3	123066	spinning	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/26 15:27
S4	385	(cleaning and (semiconductor adj wafer)) and spinning	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/21 09:28
S5	28123	hydrofluoric adj acid	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/20 13:10
S6	55	((cleaning and (semiconductor adj wafer)) and spinning) and (hydrofluoric adj acid)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/20 13:32
S7	6912	ammonium adj fluoride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/20 13:32
S8	2	(((cleaning and (semiconductor adj wafer)) and spinning) and (hydrofluoric adj acid)) and (ammonium adj fluoride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/20 13:32
S9	476476	cleaning	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/21 09:27

S10	1	(cleaning and (semiconductor adj wafer)) and spinning and (alkali adj metals)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/21 09:29
S11	16	cleaning and (semiconductor adj wafer) and (alkali adj metals)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/21 09:30
S12	103	spin adj cleaning	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/22 09:11
S13	68556	semiconductor adj wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/21 13:45
S14	24	(spin adj cleaning) and (semiconductor adj wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/21 13:57
S15	10	ammonia and (spin adj cleaning)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/21 14:00
S16	28	contaminating adj impurity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/21 14:04
S17	22	spinning near4 etchant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/21 14:12
S18	109	spin adj etching	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/21 14:12
S19	99498	contaminants	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/21 14:12

S20	5	(spin adj etching) and contaminants	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/21 14:12
S21	1413	(349/139).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/21 16:50
S22	271503	bus	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/21 16:50
S23	118	(("349/139").CCLS.) and bus	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/21 16:56
S24	40	(349/140).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/21 16:57
S25	9	bus and (("349/140").CCLS.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/21 16:57
S26	769	(349/143).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/21 16:58
S27	90	bus and (("349/143").CCLS.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/21 16:58
S28	0	"6239045".uref.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/22 08:11

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S29	2	("6239045").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/22 08:12
S30	8	(("5828080") or ("6008128")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/22 08:12
S31	24	semiconductor adj wafer and spin adj cleaning	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/22 08:15
S32	144	spin adj etching or spin adj etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/22 08:16
S33	73277	"baker"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/22 08:55
S34	294	semiconductor adj wafer and "baker"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/22 09:04
S35	820359	alkali or sodium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/22 08:57
S36	24	(semiconductor adj wafer and "baker") and (alkali or sodium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/22 09:04
S37	0	"J.T. Baker"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/22 09:04

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S38	13	((semiconductor adj wafer and "baker") and (hydrogen adj peroxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/22 09:05
S39	10	spin adj cleaning and ammonia	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/22 09:11
S40	33381	((thin adj film adj transistor) or (tft))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/23 15:02
S41	50	contamination near5 glass adj substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/22 09:23
S42	591	mobile adj ion	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/22 09:24
S43	1452	((mobile adj ion) or (mobile adj ions))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/22 09:24
S44	195290	contamination	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/22 09:24
S45	26	((((thin adj film adj transistor) or (tft))) and (((mobile adj ion) or (mobile adj ions)))) and contamination	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/22 09:24
S46	55457	glass adj substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/22 09:25
S47	19	(((((thin adj film adj transistor) or (tft))) and (((mobile adj ion) or (mobile adj ions)))) and contamination) and (glass adj substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/22 09:41

S48	1	"5578103".uref.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/22 09:41
S49	0	"perodic table group 1 element"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/22 15:58
S50	23	"group 1 element"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/22 16:04
S51	1569835	((remove) or (removal))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/22 16:05
S52	607755	((mobile adj ion) or (alkali) or (alkaline))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/22 16:06
S53	11274	(((remove) or (removal))) near4 (((mobile adj ion) or (alkali) or (alkaline)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/22 16:06
S54	12	glass adj substrate near4 ((((remove) or (removal))) near4 (((mobile adj ion) or (alkali) or (alkaline))))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/22 16:07
S55	23	((thin adj film adj transistor) or (tft)) and (((((remove) or (removal))) near4 (((mobile adj ion) or (alkali) or (alkaline))))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/22 16:16
S56	2	"5792327".uref.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/22 17:20
S57	0	"post fabrication rca cleaning"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/22 17:21

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S58	484	"post fabrication"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/22 17:21
S59	0	rca adj cleaning near4 "post fabrication"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/22 17:22
S60	0	rca adj cleaning near6 "post fabrication"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/22 17:22
S61	0	rca adj cleaning same "post fabrication"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/22 17:22
S62	66	(((thin adj film adj transistor) or (tft))) and (((mobile adj ion) or (mobile adj ions)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/23 14:59
S63	655	((thin adj film adj transistor) or (tft)) and hydrofluoric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/23 15:03
S64	238454	mobile	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/23 15:04
S65	44	(((thin adj film adj transistor) or (tft)) and hydrofluoric) and mobile	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/23 15:04
S66	362	(438/151).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2001/08/24 15:07

S67	2	("5792327").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/26 08:46
S68	3	"5792327".URPN.	USPAT	OR	ON	2002/06/26 08:47
S69	25862	tft or (thin adj film adj transitor) and alkali and (clean or cleaning)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/26 15:29
S70	160	spinning and (tft or (thin adj film adj transitor) and alkali and (clean or cleaning))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/26 15:27
S71	227	(tft or (thin adj film adj transitor)) and alkali and (clean or cleaning)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/26 18:15
S72	13	"4994415".URPN.	USPAT	OR	ON	2002/06/26 15:34
S73	53	islands and (cleaning or clean) and hf and (tft or (thin adj film adj transitor) and alkali and (clean or cleaning)) and (spin or spinning)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/26 15:57
S74	824	removal near alkali	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/26 15:58
S75	14638	semiconductor adj film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/26 15:59
S76	10	(removal near alkali) and (semiconductor adj film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/26 16:03
S77	0	(islands and (cleaning or clean) and hf and (tft or (thin adj film adj transitor) and alkali and (clean or cleaning)) and (spin or spinning)) and (removal near alkali)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/26 16:03

S78	4	"5985704".uref.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/26 16:26
S79	2	("5985704").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/26 16:47
S80	11	("4059461" | "4132571" | "4174217" | "4271422" | "4277884" | "4534820" | "4544418" | "4755481" | "5147826" | "5173446" | "5275851").PN.	USPAT	OR	ON	2002/06/26 16:27
S81	187	"5275851".URPN.	USPAT	OR	ON	2002/06/26 16:29
S82	67	ammonium adj fluoride and etching and tft and islands	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/26 16:59
S83	1	ammonium adj fluoride and "spin-etching"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/26 17:00
S84	3	fluoride and "spin-etching"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/26 17:01
S85	38	"spin-etching"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/26 17:01
S86	121	(tft or (thin adj film adj transitor)) and alkali and (clean or cleaning) and (spin or spinning)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/26 18:27
S87	2	semiconductor adj islands and tft and etching and spinning	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/26 18:28

S88	2	("5476816").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/28 09:22
S89	14	"5476816".URPN.	USPAT	OR	ON	2002/06/28 09:22
S90	10	"laurell technologies corporation" or "laurell technologies corp"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/28 09:40
S91	0	"spin etch silicon"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/28 09:40
S92	72	spin adj etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/28 09:41
S93	1140107	semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/28 09:41
S94	53	(spin adj etch) and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/28 09:41
S95	62	(438/150).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/06/28 10:54
S96	0	tft and alkali adj contaminants	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/28 10:55
S97	1028	tft and sodium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/28 10:55

S98	44059	crystallize	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/28 10:57
S99	158	(tft and sodium) and crystallize	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/28 10:57
S10 0	275235	fluoride or fluorine	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/28 10:58
S10 1	114	((tft and sodium) and crystallize) and (fluoride or fluorine)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/28 11:01
S10 2	18009	wet adj etching	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/28 11:02
S10 3	23	(((tft and sodium) and crystallize) and (fluoride or fluorine)) and (wet adj etching)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/28 11:03
S10 4	223328	spin or spinning	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/28 11:04
S10 5	10	((((tft and sodium) and crystallize) and (fluoride or fluorine)) and (wet adj etching)) and (spin or spinning)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/28 11:08
S10 6	1	thin adj film adj transistors and alkali adj contamination	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/06/28 11:09
S10 7	0	(tft or thin adj film adj transistor) and (spin adj etch)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/10/10 14:30

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S10 8	107	spin adj etch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/10/10 14:31
S10 9	50	spin adj etcher	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/27 14:20
S11 0	4	(("5494849") or ("5937312")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/27 14:21
S11 1	5031752	alkali or na sodium or k or potassium or magnesium or mg or ca or calcium or ba barium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/27 14:36
S11 2	4920135	alkali adj metal or na sodium or k or potassium or magnesium or mg or ca or calcium or ba barium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/27 14:36
S11 3	136096	etching and S112	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/27 14:38
S11 4	35654	(spin or rotate or rotary or spinning) and S113	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/27 14:55
S11 5	5418	fluoride and S114	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/27 14:39
S11 6	1266	hf and S115	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/27 14:40
S11 7	275	ammonium adj fluoride and S116	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/27 14:58

S11 8	24	("5560857").URPN.	USPAT	OR	ON	2004/12/27 14:52
S11 9	147	(spin adj etch or spin adj etching or spin adj etcher) and S112	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/27 14:56
S12 0	7	ammonium adj fluoride and S119	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/27 14:58
S12 1	4	("4339340").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/27 17:03
S12 2	29	("4339340").URPN.	USPAT	OR	ON	2004/12/27 17:04
S12 3	53	("5129955").URPN.	USPAT	OR	ON	2004/12/27 17:09
S12 4	105350	(tft or thin adj film adj transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 12:27
S12 5	432	spin adj etch or spin adj etching	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 12:27
S12 6	17	S124 and S125	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 12:27
S12 7	2	("6127279").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/25 10:49

S12 8	1651	(438/151).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2007/05/24 12:41
S12 9	493	(438/704).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2007/05/24 12:55
S13 0	165	(438/716).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2007/05/24 13:00
S13 1	1	(etching adj solution and spinning and resist and gate).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/24 13:01